

UROP PROJECT
SRM UNIVERSITY 2024-25

BANDGAP REFERENCE CIRCUIT

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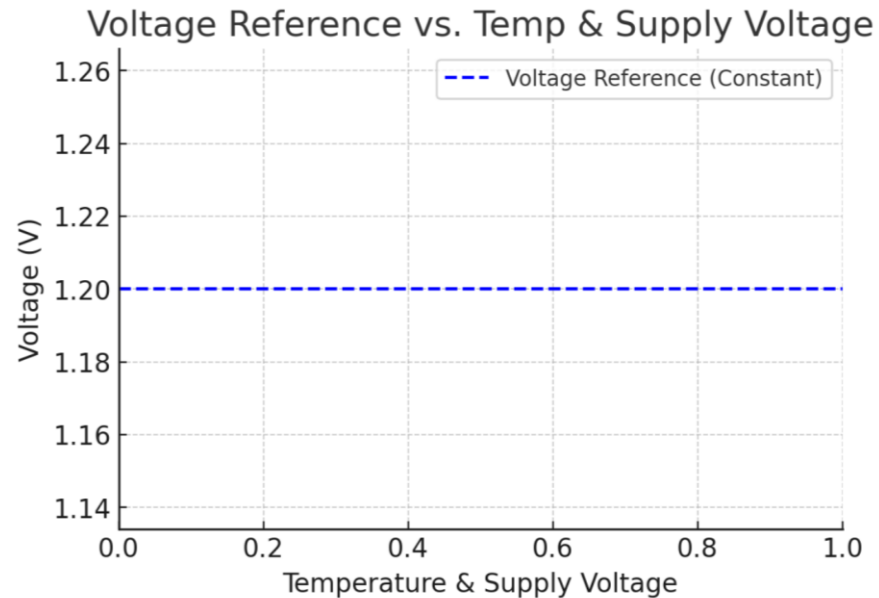
Problem Statement:

Designing Bandgap Reference Circuit

Literature Review

Bandgap Reference Circuit:

A **bandgap reference** is a circuit that generates a stable voltage reference independent of variations in power supply voltage, temperature, and transistor properties. The principle behind this circuit is based on the thermal voltage dependency of bipolar junction transistors (BJTs).

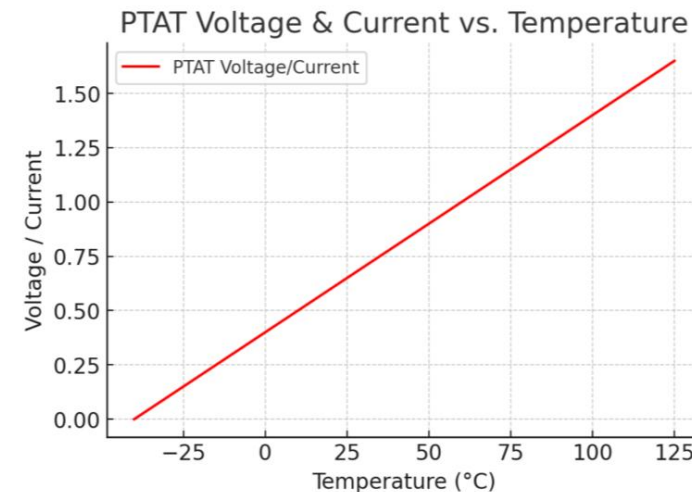


PTAT (Proportional to Absolute Temperature):

PTAT voltage or current increases **linearly** with temperature. It is derived from the difference in base-emitter voltages of two BJTs operating at different current densities.

Applications:

- Temperature sensors
- Biasing circuits in analog ICs
- Compensation techniques in voltage references

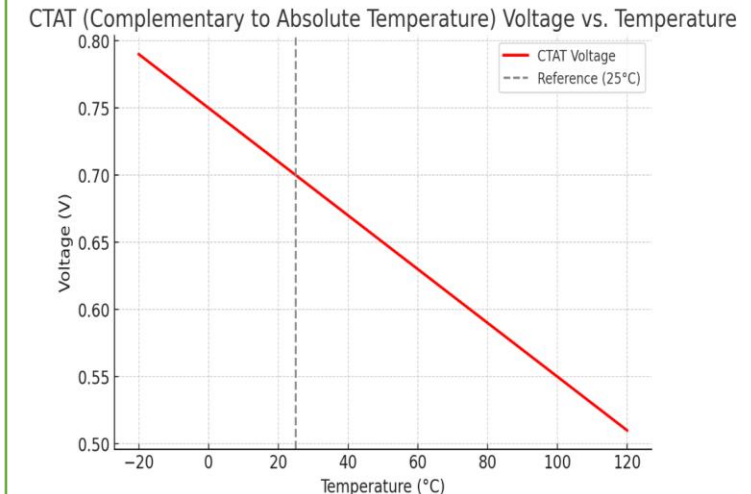


Complementary to Absolute Temperature (CTAT) Voltage:

CTAT voltage refers to a voltage that **decreases as temperature increases**. It is the opposite of PTAT (Proportional to Absolute Temperature) voltage.

Application:

- 1.Bandgap Reference Circuits.
- 2.Temperature Compensation.
- 3.Biasing Circuits.
- 4.Power Management Ics.



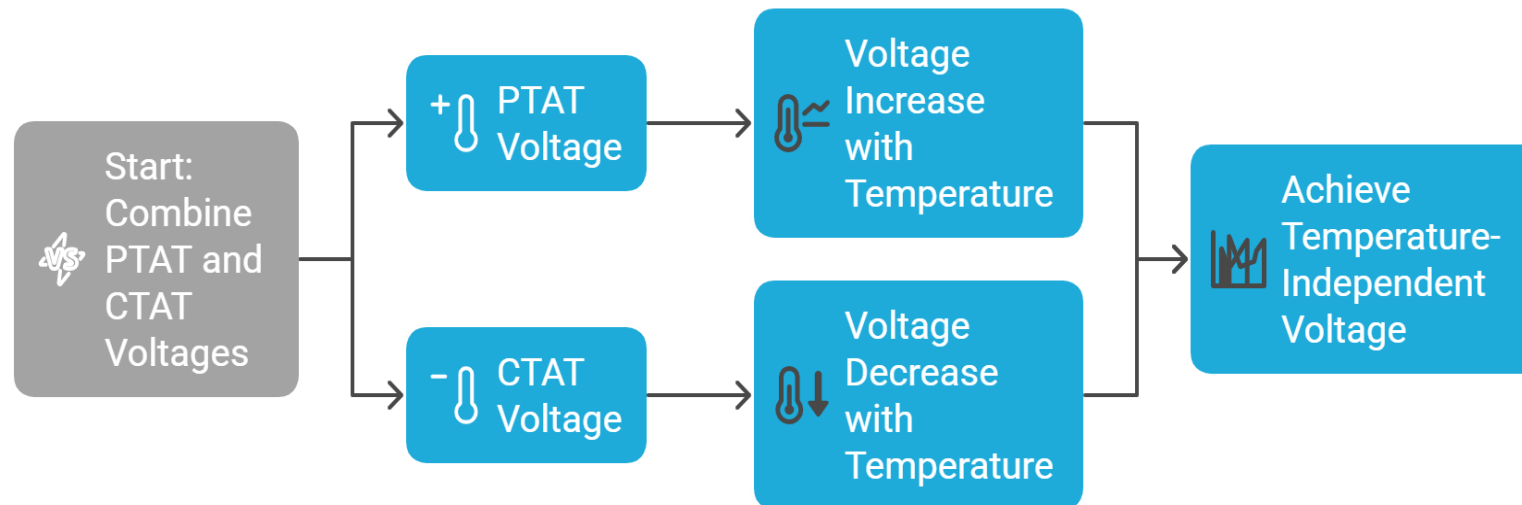
WORKING PRINCIPLE AND BLOCK DIAGRAM:

A bandgap reference circuit typically combines two voltage sources:

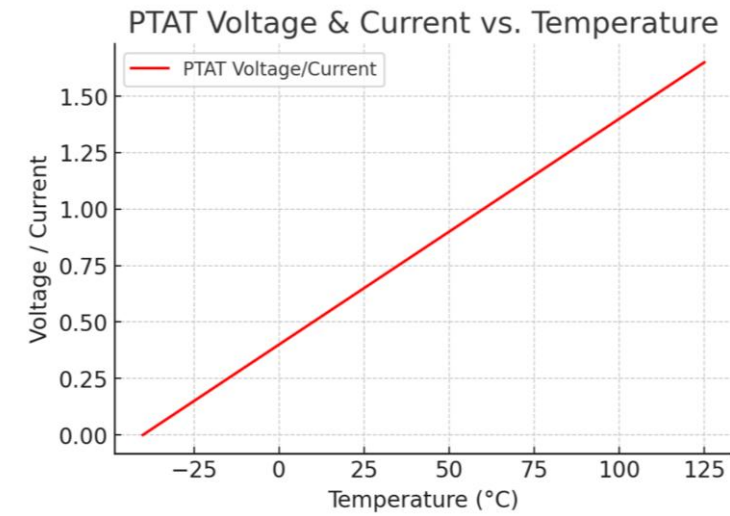
1. **PTAT (Proportional to Absolute Temperature) Voltage** – This voltage increases with temperature.
 2. **CTAT (Complementary to Absolute Temperature) Voltage** – This voltage decreases with temperature.
- By adding PTAT and CTAT voltages, a nearly **temperature-independent voltage** is achieved.

Addition of PTAT and CTAT => $\alpha_1 PTAT + \alpha_2 CTAT = \text{Constant Voltage}$

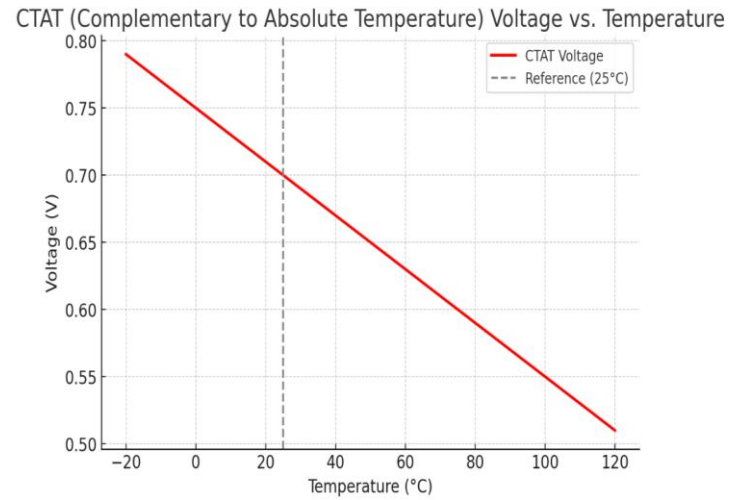
Bandgap Reference Circuit Process



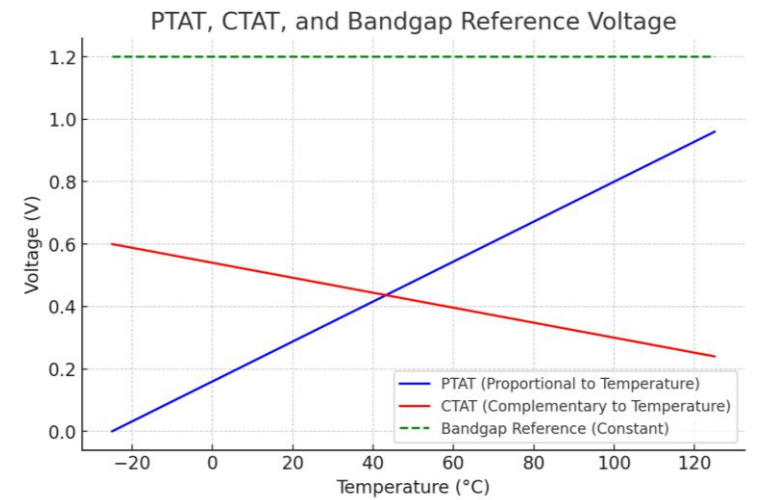
Addition of PTAT and CTAT => $\alpha_1 PTAT + \alpha_2 CTAT = \text{Constant Voltage}$



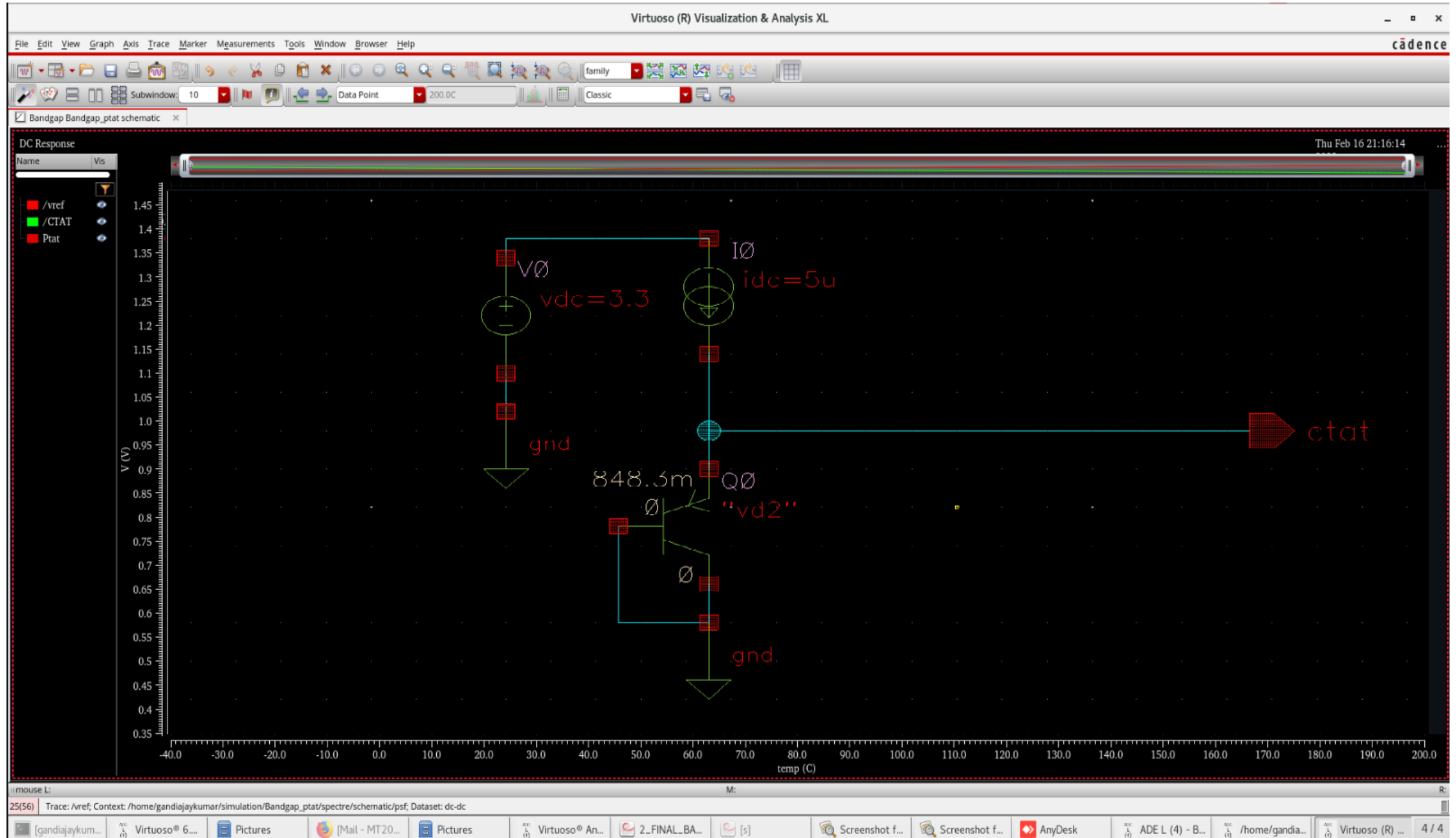
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Schematic Analysis Of CTAT



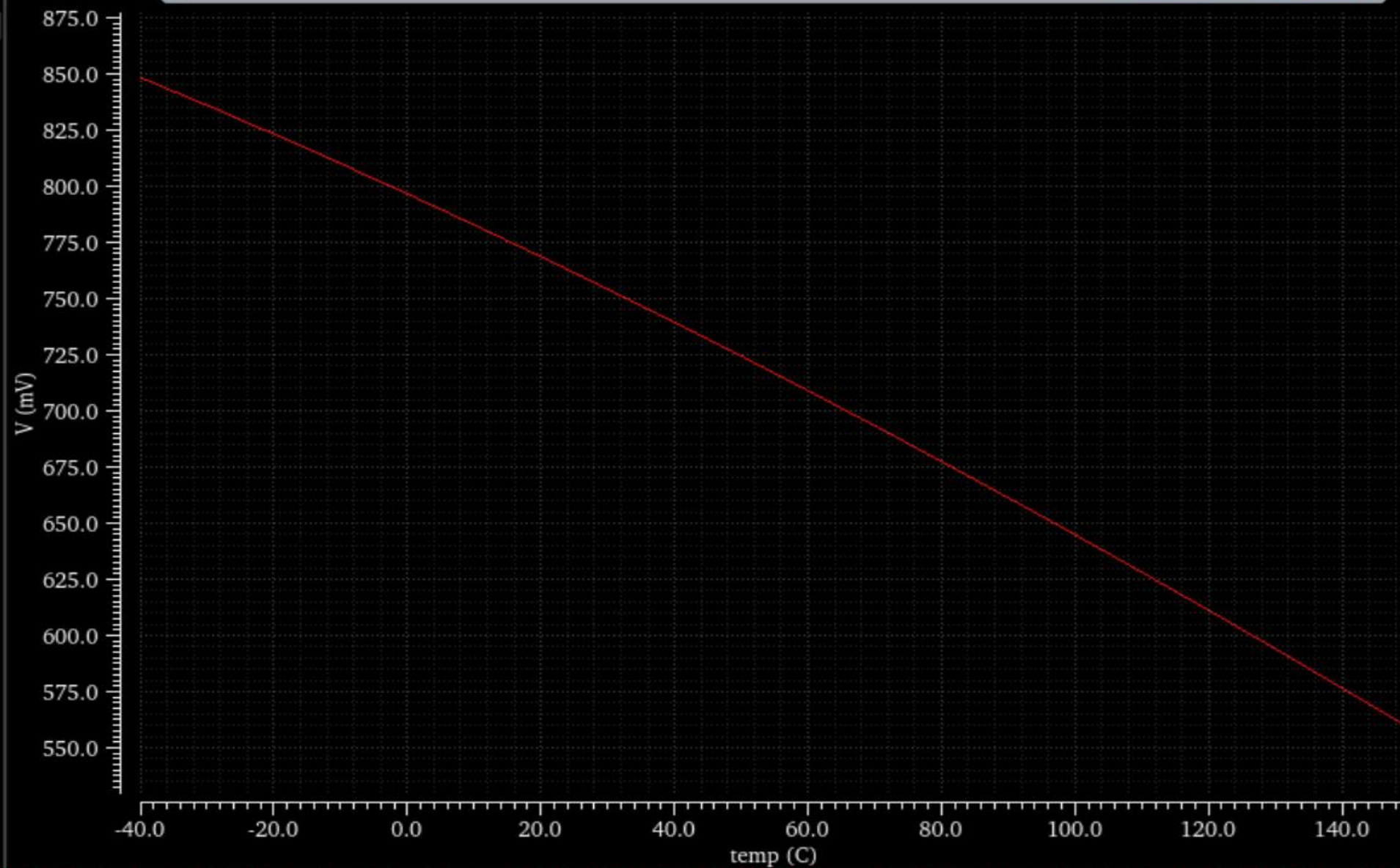
DC Response

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References

- https://www.youtube.com/watch?v=aynJSMErq4g&list=PLK2eyR1C9gjp5tk5j7eTYU_Th4IL_H83T&index=3
- https://www.researchgate.net/publication/382569345_Research_Progress_of_Bandgap_Reference_Circuit

Research Progress of Bandgap Reference Circuit

Abstract. As an important part of integrated circuit design, bandgap reference circuit is widely used in various chips, among which ADC (analog-to-digital converter) and DAC(digital-to-analog converter) are typical examples. This paper introduces the bandgap reference circuit and its working principle in detail, and then systematically combs and introduces a variety of bandgap reference circuits. A conventional bandgap reference circuit consists of an op-amp, two bipolar transistors and multiple resistors; The CMOS bandgap reference circuit uses the common-source common-gate current mirror to provide the bias current to reduce the power consumption and the channel length modulation effect so that the circuit can work at a lower supply voltage. A bandgap reference circuit using PTAT (proportional to absolute temperature) current to generate reference voltages with different temperature coefficients can produce a simpler circuit structure than the traditional bandgap reference circuit. By summarizing and comparing these bandgap reference circuits, the latest trends and technical trends in this field are presented, providing guidance and inspiration for future research work.

Keywords: PTAT; bandgap reference circuit; cascade current mirror.

Future Work:

- Schematic and Design Analysis of the PTAT.
- Combining the ptat and ctat to get the full band gap circuit.

Notes:

Bandgap Reference Circuit:-

Its function is to provide constant reference voltage that is independent of temperature and supply voltage.

According to the industry:- the temperature varies from -40°C to 125°C

Conclusion:- As a bandgap reference circuit it should maintain constant output voltage with respect to the supply voltage and other variation parameters.

Supply variation and temperature variation:-

Some of the voltages and currents will increase as we increase the temperature. This type of voltage and current are called PTAT.

PTAT:- Proportional to absolute temperature. It could be voltage or current.

Block diagram:-

Now, we need two things:- PTAT and CTAT

① **CTAT:-** Complementary to absolute temperature.

- If the temperature increases then the voltage decreases.
- If we pass a current through a diode then it produces voltage.

$I_0 = I_s \cdot e^{V_0/V_T}$

$I_0 = I_s \cdot e^{V_0/(kT/q)}$

$V_0 = V_T \ln\left(\frac{I_0}{I_s}\right)$ across the diode. ①

$V_D = V_T \ln\left(\frac{I_0}{I_s}\right) = V_{PTAT}$

$\frac{dV_D}{dT} = -1.6 \text{ mV}/^{\circ}\text{C}$

$V_T = \frac{kT}{q}$

$\frac{dV_T}{dT} = \frac{k}{q} \rightarrow \text{PTAT} \text{ --- ②}$

$\ln(I_0/I_s) \cdot V_T = \text{Constant with respect to temperature}$

I_s is state current of transistor and intrinsic.

$I_s \propto A \cdot k \cdot T \cdot e^{-E_g/kT}$

$I_s \propto T^{4+m} \cdot \exp[-E_g/kT] \text{ --- equation ③}$

$I_s = b \cdot T^{4+m} \cdot \exp[-E_g/kT] \text{ --- ④}$

Now we are going to see how current is changing with respect to temperature.

$\frac{dI_s}{dT} = b \left[T^{4+m} \cdot \exp[-E_g/kT] \cdot \left(\frac{4+m}{T} + \frac{E_g}{kT^2} \right) \right]$

using this argument there will be no substrate current.

Designing of PTAT:- Proportional to absolute temperature.

$V_T = \frac{kT}{q}$

$V_D \propto T$

$V_D = V_T \ln(I_0/I_s)$

$V_D = V_T \ln\left(\frac{I_0}{I_s}\right)$

So, as we know CTAT is more dominating than PTAT because CTAT has factor 4.5 times because of which it is more.

So, our requirement is to get PTAT so any how if we are able to remove CTAT.

$V_D = V_T$

$V_D = V_0 = V_T$

CTAT:- Complementary to absolute temperature.

Decreases with increase in temperature.

Now we need constant voltage.

If we cancel the effect of PTAT and CTAT, then we get constant voltage.

add PTAT and CTAT:-

$(\alpha_1 \text{PTAT} + \alpha_2 \text{CTAT}) = \text{const. voltage}$

We will adjust α_1 and α_2 so that when we will adjust α_1 and α_2 then we can adjust these curves and get the constant voltage.

$\alpha_1 \text{PTAT} + \alpha_2 \text{CTAT} = \text{constant voltage}$

How to make diode:-

So, if we want to make diode using CMOS then:-

Polysilicon should be connected to the same current source and it should be with ground.

But in CMOS P-substrate is always grounded. So, we have to use some other device.

So, this is BJT and it will affect the output voltage.

$V_D = V_T \ln\left(\frac{I_0}{I_s}\right)$

$V_{D1} = V_T \ln\left(\frac{I_0}{I_{s1}}\right)$

Now, substrate:-

$V_D = V_{D1} = V_T \ln\left(\frac{I_0}{I_{s1}}\right) = V_T \ln\left(\frac{I_0}{I_s} \cdot \frac{I_s}{I_{s1}}\right)$

$V_D - V_{D1} = V_T \ln\left(\frac{I_s}{I_{s1}}\right)$

$V_D - V_{D1} = V_T \ln\left(\frac{I_s}{I_{s1}}\right)$

constant N_A and deg of carrier profile constant.

$\text{const} = \ln\left(\frac{I_s}{I_{s1}}\right)$

So, we can see that $V_D - V_{D1}$ is proportional to T and constant. It is T .